

# Sung Heo

## List of Publications by Year in descending order

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27  
papers

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citations

840776

11  
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28  
docs citations

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times ranked

736  
citing authors

#	ARTICLE	IF	CITATIONS
1	Short-circuit mechanism induced by crack propagation spurred by inhomogeneous electric field in garnet-based solid electrolyte. <i>Journal of Power Sources</i> , 2021, 510, 230389.	7.8	5
2	In-Depth Investigation of the Correlation between Organic Semiconductor Orientation and Energy-Level Alignment Using In Situ Photoelectron Spectroscopy. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 50628-50637.	8.0	5
3	Origin of intergranular Li metal propagation in garnet-based solid electrolyte by direct electronic structure analysis and performance improvement by bandgap engineering. <i>Journal of Materials Chemistry A</i> , 2020, 8, 16892-16901.	10.3	24
4	Simple and effective cleaning method for RuO <sub>2</sub> nanosheet films for flexible transparent conducting electrodes. <i>Applied Surface Science</i> , 2020, 529, 147154.	6.1	5
5	Surface plasmon enhanced Organic color image sensor with Ag nanoparticles coated with silicon oxynitride. <i>Scientific Reports</i> , 2020, 10, 219.	3.3	7
6	<i>In situ</i> observation of lithium metal plating in a sulfur-based solid electrolyte for all-solid-state batteries. <i>Journal of Materials Chemistry A</i> , 2019, 7, 13650-13657.	10.3	45
7	The role of defects in organic image sensors for green photodiode. <i>Scientific Reports</i> , 2019, 9, 1745.	3.3	7
8	Atomic layer-deposited (HfZrO <sub>4</sub> ) <sub>1-x</sub> (SiO <sub>2</sub> ) <sub>x</sub> thin films for gate stack applications. <i>Thin Solid Films</i> , 2018, 652, 2-9.	1.8	0
9	Experimental study on solid electrolyte interphase of graphite electrode in Li-ion battery by surface analysis technique. <i>Molecular Crystals and Liquid Crystals</i> , 2018, 663, 158-167.	0.9	3
10	Device performance enhancement via a Si-rich silicon oxynitride buffer layer for the organic photodetecting device. <i>Scientific Reports</i> , 2017, 7, 1516.	3.3	10
11	Direct evidence of flat band voltage shift for TiN/LaO or ZrO/SiO <sub>2</sub> stack structure via work function depth profiling. <i>Scientific Reports</i> , 2017, 7, 43561.	3.3	2
12	Effective work function engineering for a TiN/XO(X=La, Zr, Al)/SiO <sub>2</sub> stack structures. <i>Applied Physics Letters</i> , 2016, 108, 212102.	3.3	3
13	Defect states in amorphous SiN <sub>x</sub> :H compounds using thermally stimulated exo-electron emission. <i>Thin Solid Films</i> , 2016, 616, 850-855.	1.8	3
14	Dark current reduction of small molecule organic photodetectors by controlling gap states of molybdenum oxide buffer layers. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 091601.	1.5	2
15	Defect visualization of Cu(InGa)(SeS) <sub>2</sub> thin films using DLTS measurement. <i>Scientific Reports</i> , 2016, 6, 30554.	3.3	22
16	Band alignment of atomic layer deposited (HfZrO <sub>4</sub> ) <sub>1-x</sub> (SiO <sub>2</sub> ) <sub>x</sub> gate dielectrics on Si (100). <i>Applied Physics Letters</i> , 2015, 107, .	3.3	27
17	Band gap and defect states of MgO thin films investigated using reflection electron energy loss spectroscopy. <i>AIP Advances</i> , 2015, 5, .	1.3	81
18	Direct evidence of void passivation in Cu(InGa)(SSe) <sub>2</sub> absorber layers. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	11

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19	Direct band gap measurement of Cu(In,Ga)(Se,S) <sub>2</sub> thin films using high-resolution reflection electron energy loss spectroscopy. Applied Physics Letters, 2015, 106, .	3.3	2
20	Damage profiles of Si (001) surface via Ar cluster beam sputtering. Surface and Interface Analysis, 2013, 45, 150-153.	1.8	10
21	Reflection electron energy loss spectroscopy for ultrathin gate oxide materials. Surface and Interface Analysis, 2012, 44, 623-627.	1.8	50
22	Band alignment and optical properties of (ZrO <sub>2</sub> ) <sub>0.66</sub> (HfO <sub>2</sub> ) <sub>0.34</sub> gate dielectrics thin films on Si (100). Journal of Surface Analysis (Online), 2011, 17, 203-207.	0.1	4
23	Electronic and optical properties of GIZO thin film grown on SiO <sub>2</sub> /Si substrates. Surface and Interface Analysis, 2010, 42, 906-910.	1.8	17
24	Electronic and optical properties of LaAl <sub>3</sub> Aluminate dielectric thin films on Si (100). Surface and Interface Analysis, 2010, 42, 1566-1569.	1.8	21
25	Band alignment of atomic layer deposited (ZrO <sub>2</sub> ) <sub>x</sub> (SiO <sub>2</sub> ) <sub>1-x</sub> gate dielectrics on Si (100). Applied Physics Letters, 2009, 94, 212902.	3.3	47
26	Dielectric and optical properties of Zr silicate thin films grown on Si(100) by atomic layer deposition. Journal of Applied Physics, 2009, 106, 084108.	2.5	25
27	Band gap engineering for La aluminate dielectrics on Si (100). Applied Physics Letters, 2008, 93, 052904.	3.3	15